To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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   Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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HSM276AS

Silicon Schottky Barrier Diode for Balanced Mixer

ADE-208-839 (Z)

Rev. 0
Feb. 2000

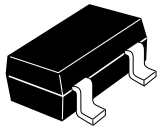
Features

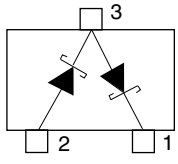
- High forward current, Low capacitance.
- HSM276AS which is interconnected in series configuration is designed for balanced mixer use.
- MPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSM276AS	S19	MPAK

Pin Arrangement





(Top View)

1 Cathode 2
2 Anode 1
3 Cathode 1
Anode 2

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	5	V
Reverse voltage	V_R	3	V
Average rectified current	I_O *	30	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55 to +125	°C

Note: Per one device

Electrical Characteristics *2

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse voltage	V_R	3.0	—	—	V	I_R = 1 mA
Reverse current	I_R	—	—	50	µA	V_R = 0.5V
Forward current	I_F	35	—	—	mA	V_F = 0.5V
Capacitance	C	—	—	0.90	pF	V_R = 0.5V, f = 1 MHz
Capacitance deviation	Δ C	—	—	0.10	pF	V_R = 0.5V, f = 1 MHz
ESD-Capability*1	—	30	—	—	V	C=200pF , R = 0 Ω Both forward and reverse direction 1pulse.

Notes: 1. Failure criterion ; $I_R \geq 100\mu A$ at V_R =0.5 V
2. Per one device

Main Characteristic

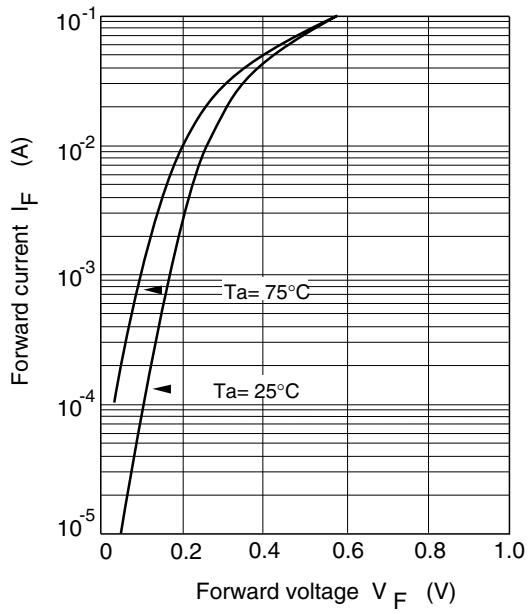


Fig.1 Forward current Vs. Forward voltage

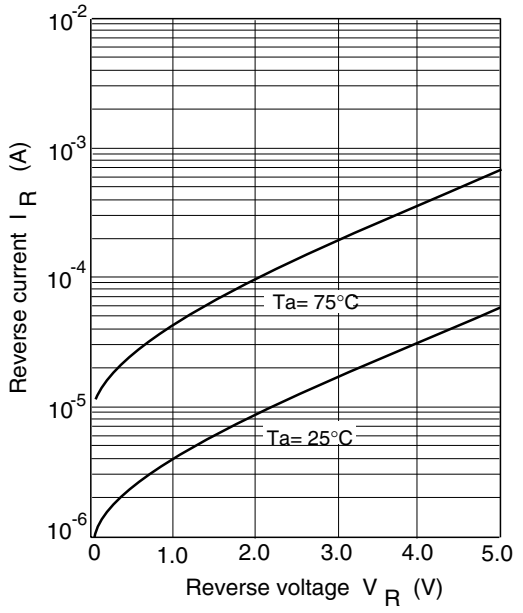


Fig.2 Reverse current Vs. Reverse voltage

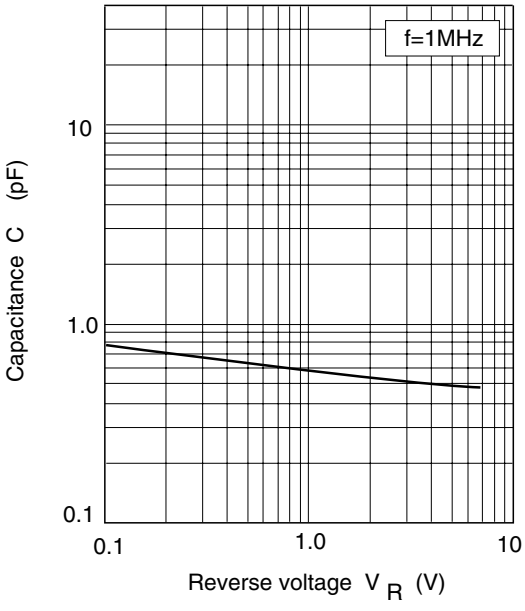
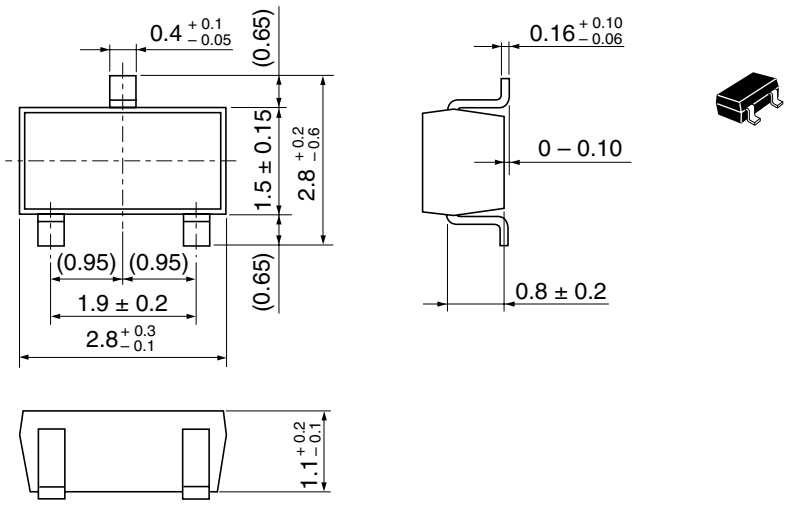


Fig.3 Capacitance Vs. Reverse voltage

Package Dimensions

Unit: mm



Hitachi Code	MPAK
JEDEC	—
EIAJ	Conforms
Mass	0.011 g

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